What Is Claimed Is:

1. A method of forming a titanium nitride thin film on a substrate disposed on a susceptor in a reaction chamber, comprising:

feeding vapor of a Tetrakis Diethylamino Titanium (TDEAT) precursor and ammonia (NH₃) gas into the reaction chamber, wherein a ratio of a vaporization rate of the TDEAT precursor to a flow rate of the ammonia gas is a value in the range of 1 mg/min: 20 secon to 1 mg/min: 100 secon;

maintaining an atmosphere in the reaction chamber at a pressure in the range of 0.5 to 3.0 Torr; and

heating the substrate to a temperature in the range of 300 to 400 degrees Celsius (°C).

- 2. The method of Claim 1, wherein the substrate is heated up to a temperature in the range of 320 to 380 degrees Celsius (°C).
- 3. The method of Claim 1, wherein the atmosphere in the reaction chamber has a pressure in the range of 0.5 to 1.5 Torr.
- 4. The method of Claim 1, further comprising supplying a carrier gas into the reaction chamber.
- 5. The method of Claim 4, wherein the carrier gag is an inert gas selected from a group consisting of argon (Ar) and helium (He).
- 6. The method of Claim 4, wherein the carrier gas is supplied at a flow rate in the range of

100 to 1000 sccm.

- 7. The method of Claim 1, further comprising vaporizing the TDEAT precursor before the TDEAT precursor is fed into the reaction chamber.
- 8. The method of Claim 7, wherein the TDEAT precursor is vaporized at a vaporization rate in a range of 10 to 50 mg/min.
- 9. The method of Claim 1, wherein the ammonia gas is fed to the reaction chamber at a flow rate in the range of 500 to 3000 secm.
- 10. The method of claim 1, wherein the reaction chamber has a dome-shaped top portion and includes a plurality of gas injectors.
- 11. The method of Claim 10, wherein the plurality of gas injectors supply the TDEAT vapor and the ammonia gas to the reaction chamber.
- 12. The method of Claim 11, wherein the TDEAT vapor and the ammonia gas are supplied in an upward direction from the bottom to top portion of the reaction chamber:
- 13. The method of Claim 11, wherein the TDEAT vapor and the ammonia gas are respectively supplied by the different gas injectors.
- 14. The method of Claim 1, wherein the reaction chamber includes a heat exchanger on an

outer surface thereof.

- 15. The method of Claim 14, wherein the heat exchanger maintains a top portion of the reaction chamber at a temperature in the range of 50 to 150 degrees Celsius (°C).
- 16. The method of Claim 15, wherein the heat exchanger maintains a top portion of the reaction chamber at a temperature in the range of 80 to 100 degrees Celsius (°C).
- 17. The method of Claim 14, wherein the heat exchanger maintains a wall of the reaction chamber at a temperature in the range of 50 to 150 degrees Celsius (°C).
- 18. The method of Claim 17, wherein the heat exchanger maintains a wall of the reaction chamber at a temperature in the range of 80 to 100 degrees Celsius (°C).

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